Micro Commercial Components
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2SC2246

NPN Silicon Power Transistors

Features

- Particularly suited for 115 and 220 voltolize operated switch-mode applications
- With TO-3 package
- High voltage, high speed power switching in inductive circuitous

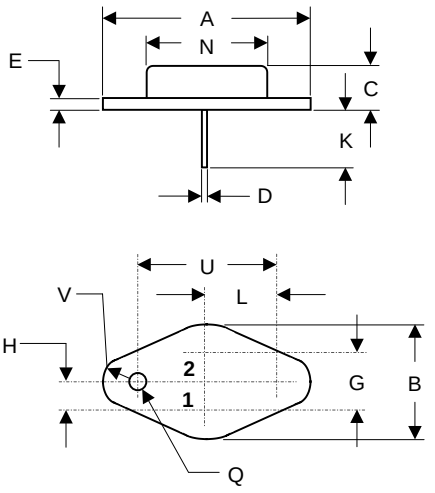
Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	400	V
V_{CBO}	Collector-Base Voltage	850	V
V_{EBO}	Emitter-Base Voltage	9.0	V
I_{CP}	Peak Collector Current	30	A
I_C	Collector Current	15	A
P_C	Collector power dissipation	175	W
T_J	Junction Temperature	-55 to +150	^{O}C
T_{STG}	Storage Temperature	-55 to +150	^{O}C

Electrical Characteristics @ 25^{0}C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (I_C=100mAdc, I_B=0)	400	---	Vdc
I_{CBO}	Collector-Base Cutoff Current (V_{CB}=850Vdc, $V_{BE(off)}$=1.5Vdc)	---	1.0	mAdc
I_{EBO}	Emitter-Base Cutoff Current (V_{EB}=9.0Vdc, I_C=0)	---	1.0	mAdc
ON CHARACTERISTICS				
h_{FE-1}	Forward Current Transfer ratio (I_C=5.0Adc, V_{CE}=2.0Vdc)	12	60	---
h_{FE-2}	Forward Current Transfer ratio (I_C=10Adc, V_{CE}=2.0Vdc)	6.0	30	---
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage (I_C=10Adc, I_B=2.0Adc)	---	1.5	Vdc
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage (I_C=15Adc, I_B=3.0Adc)	---	5.0	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage (I_C=10Adc,I_B=2.0Adc)	---	1.6	Vdc
f_T	Transition Frequency (I_C=0.5Adc, V_{CE}=10Vdc, f=1.0MHz)	6.0	28	MHz

TO-3



PIN 1. BASE
PIN 2. EMITTER
CASE. COLLECTOR

DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	1.550	REF	39.37	REF	
B	-----	1.050	-----	26.67	
C	.250	.335	6.35	8.51	
D	.038	.043	0.97	1.09	
E	0.55	0.70	1.40	1.77	
G	.430	BSC	10.92	BSC	
H	.215	BSC	5.46	BSC	
K	.440	.480	11.18	12.19	
L	.665	BSC	16.89	BSC	
N	-----	.830	-----	21.08	
Q	.151	.165	3.84	4.19	∅
U	1.187	BSC	30.15	BSC	
V	.131	.188	3.33	4.77	